

IN THE SPECIFICATION:

Please replace the paragraph at page 6, line 26, through page 7, line 6, with the following rewritten paragraph:

-- U.S. Patent ~~Application, Serial No. 08/855,059~~ No. 6,605,197, of the present applicants, ~~filed May 13, 1997, issued August 12, 2003~~, describes a method of filling features on a semiconductor workpiece surface with copper using sputtering techniques. The surface temperature of the substrate is controlled within particular temperature ranges during application of the copper layer. The sputtering method is selected from a number of potential sputtering methods, including gamma sputtering, coherent sputtering, IMP (ion metal plasma), and traditional sputtering, all of which are described in detail. The content of ~~Application Serial No. 08/855,059~~ U.S. Patent No. 6,605,197 is hereby incorporated by reference in its entirety. --

Please replace the paragraph at page 12, lines 14 - 17, with the following rewritten paragraph:

-- Figure 1 shows a schematic of a cross-sectional view of a contact via including a multiple-layered barrier layer overlaid with a metallic conductive layer. Figure 1 is a prior art drawing taken from U.S. Patent ~~Application, Serial No. 08/511,825~~ of No. 5,962,923, issued October 5, 1999, to Xu et al. , which patent is assigned to the assignee of the present invention. --